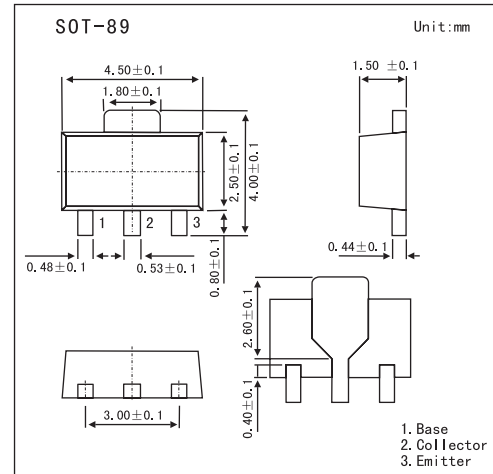


Silicon PNP Epitaxial

2SA1944

■ Features

- High voltage $V_{CE0}=-50V$
- Low collector to emitter saturation voltage
 $V_{CE(sat)}=-0.2v$ typ (@ $I_C=-500mA$, $I_B=-10mA$)
- High h_{FE} : $h_{FE}=400$ to 800
- Small package for mounting

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Emitter-base voltage	V_{EBO}	-6	V
Collector-emitter voltage	V_{CEO}	-50	V
Peak collector current	I_{CM}	-2	A
Collector current	I_C	-1	A
Collector dissipation ($T_a=25^\circ C$)	P_C	500	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-6			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-50			V
Collector cutoff current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=-2V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-100mA$	400		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-10mA$		-0.2	-0.5	V
Gain bandwidth product	f_T	$V_{CE}=-10V, I_E=-10mA$		90		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		30		pF

■ Marking

Marking	XG
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